Amendments to the Claims:

1. (Currently Amended): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an exposed ~~oxide containing~~ oxide-containing surface;

treating the exposed ~~oxide containing~~ oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane; and

~~depositing~~ forming a second capacitor electrode over the treated ~~oxide containing~~ oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated ~~oxide containing~~ oxide-containing surface.

2. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of semiconductive material.

3. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of metal.

4. (Currently Amended): The method of claim 1 wherein the exposed ~~oxide containing~~ oxide-containing surface comprises hafnium oxide.

5. (Currently Amended): The method of claim 1 wherein the exposed ~~oxide-containing~~ oxide-containing surface comprises aluminum oxide.

6. (Original): The method of claim 1 wherein the treating is with at least one borane.

7. (Original): The method of claim 6 wherein all borane used during the treating is void of halogen.

8. (Original): The method of claim 6 wherein the borane is selected from the group consisting of BH_3, B_2H_6, B_4H_{10}, B_5H_9, B_6H_{10} and $B_{10}H_{14}$, and mixtures thereof.

9. (Original): The method of claim 1 wherein the treating is with at least one silane.

10. (Original): The method of claim 9 wherein all silane used during the treating is void of halogen.

11. (Original): The method of claim 9 wherein the silane is selected from the group consisting of SiH_4, Si_2H_6, Si_3H_8 and Si_4H_{10}, and mixtures thereof.

12. (Original): The method of claim 1 wherein any layer deposited by the treating is no more than 3 monolayers thick.

13. (Original): The method of claim 12 wherein no layer is deposited by the treating.

14. (Currently Amended): The method of claim 1 wherein the exposed ~~oxide-containing~~ oxide-containing surface comprises hafnium oxide, and wherein any layer deposited by the treating is no more than 3 monolayers thick.

15. (Currently Amended): The method of claim 1 wherein the exposed ~~oxide-containing~~ oxide-containing surface comprises aluminum oxide, and wherein any layer deposited by the treating is no more than 3 monolayers thick.

16. (Original): The method of claim 1 wherein the treating comprises a temperature from 200°C to 500°C, and a pressure from 1 Torr to 100 Torr.

17. (Original): The method of claim 1 wherein the treating is for at least 1 second.

18. (Original): The method of claim 1 wherein the treating is for at least 10 seconds.

19. (Original): The method of claim 1 wherein the inner metal surface comprises an elemental metal or an alloy of elemental metals.

20. (Original): The method of claim 19 wherein the inner metal surface comprises tungsten.

21. (Original): The method of claim 1 wherein the inner metal surface comprises a conductive metal compound.

22. (Original): The method of claim 21 wherein the inner metal surface comprises TiN.

23. (Original): The method of claim 1 wherein the second capacitor electrode consists essentially of metal.

24. (Original): The method of claim 1 wherein the treating is effective to reduce leakage current of the capacitor than would otherwise occur in the absence of said treating.

25. (Currently Amended): The method of claim 1 wherein the exposed ~~oxide surface~~ oxide-containing surface comprises OH groups, the treating being effective to passivate said OH groups.

26. (Currently Amended): The method of claim 1 wherein the depositing the second capacitor electrode comprises using a ~~halogen containing~~ halogen-containing gas, the treating being effective to reduce halogen incorporation into the capacitor dielectric region than would otherwise occur in the absence of said treating.

27. (Original): The method of claim 1 wherein,

forming the capacitor dielectric region comprises deposition of multiple dielectric layers; and

intermediate at least some of the dielectric layer depositions, treating an outer surface of the capacitor dielectric region being formed with at least one of a borane or a silane.

28. (Original): The method of claim 27 wherein the treating is with at least one borane.

29. (Original): The method of claim 27 wherein the treating is with at least one silane.

30. (Original): The method of claim 27 wherein the multiple dielectric layers comprise at least two different dielectric materials.

31. (Original): The method of claim 27 wherein the multiple dielectric layers are of the same dielectric material.

32. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of semiconductive material and the second capacitor electrode consists essentially of metal thereby forming an MIS capacitor.

33. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of metal and the second capacitor electrode consists essentially of metal thereby forming an MIM capacitor.

34. (Currently Amended): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an exposed ~~oxide-containing~~ oxide-containing surface;

treating the exposed ~~oxide-containing~~ oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane at a temperature from 200°C to 500°C and a pressure from 1 Torr to 100 Torr for at least 1 second, any layer deposited by the treating being no more than 3 monolayers thick; and

~~depositing~~ forming a second capacitor electrode consisting essentially of metal over the treated ~~oxide-containing~~ oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated ~~oxide-containing~~ oxide-containing surface.

35. (Currently Amended): The method of claim 34 wherein the exposed ~~oxide-containing~~ oxide-containing surface comprises hafnium oxide.

36. (Currently Amended): The method of claim 34 wherein the exposed ~~oxide-containing~~ oxide-containing surface comprises aluminum oxide.

37. (Original): The method of claim 34 wherein the treating is with at least one borane.

38. (Original): The method of claim 37 wherein all borane used during the treating is void of halogen.

39. (Original): The method of claim 37 wherein the borane is selected from the group consisting of BH_3, B_2H_6, B_4H_{10}, B_5H_9, B_6H_{10} and $B_{10}H_{14}$, and mixtures thereof.

40. (Original): The method of claim 34 wherein the treating is with at least one silane.

41. (Original): The method of claim 40 wherein all silane used during the treating is void of halogen.

42. (Original): The method of claim 40 wherein the silane is selected from the group consisting of SiH_4, Si_2H_6, Si_3H_8 and Si_4H_{10}, and mixtures thereof.

43. (Original): The method of claim 34 wherein no layer is deposited by the treating.

44. (Original): The method of claim 34 wherein the treating is for at least 10 seconds.

45. (Original): The method of claim 34 wherein the inner metal surface comprises an elemental metal or an alloy of elemental metals.

46. (Original): The method of claim 45 wherein the inner metal surface comprises tungsten.

47. (Original): The method of claim 34 wherein the inner metal surface comprises a conductive metal compound.

48. (Original): The method of claim 47 wherein the inner metal surface comprises TiN.

49. (Original): The method of claim 34 wherein the treating is effective to reduce leakage current of the capacitor than would otherwise occur in the absence of said treating.

50. (Currently Amended): The method of claim 34 wherein the exposed ~~oxide surface~~ oxide-containing surface comprises OH groups, the treating being effective to passivate said OH groups.

51. (Currently Amended): The method of claim 34 wherein the depositing the second capacitor electrode comprises using a ~~halogen containing~~ halogen-containing gas, the treating being effective to reduce halogen incorporation into the capacitor dielectric region than would otherwise occur in the absence of said treating.

52. (Original): The method of claim 34 wherein,

forming the capacitor dielectric region comprises deposition of multiple dielectric layers; and

intermediate at least some of the dielectric layer depositions, treating an outer surface of the capacitor dielectric region being formed with at least one of a borane or a silane.

53. (Original): The method of claim 52 wherein the multiple dielectric layers comprise at least two different dielectric materials.

54. (Original): The method of claim 52 wherein the multiple dielectric layers are of the same dielectric material.

Cancel claims 55-96.

97. (New): The method of claim 12 wherein a layer no more than 3 monolayers thick is deposited by the treating.

98. (New): The method of claim 34 wherein a layer no more than 3 monolayers thick is deposited by the treating.

99. (New): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate, the first capacitor electrode comprising an exposed metal surface;

treating the exposed metal surface of the first capacitor electrode with at least one of a borane or a silane;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an oxide-containing surface received contacting against the treated metal surface of the first capacitor electrode, the capacitor dielectric region comprising an exposed oxide-containing surface;

treating the exposed oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane; and

forming a second capacitor electrode over the treated oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated oxide-containing surface.

100. (New): A method of forming a capacitor, comprising:

forming a first capacitor electrode consisting essentially of metal over a semiconductor substrate, the first capacitor electrode comprising an exposed metal surface;

treating the exposed metal surface of the first capacitor electrode with at least one of a borane or a silane at a temperature from 200°C to 500°C and a pressure from 1 Torr to 100 Torr for at least 1 second, any layer deposited by the treating being no more than 3 monolayers thick.;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an oxide-containing surface received contacting against the treated metal surface of the first capacitor electrode, the capacitor dielectric region comprising an exposed oxide-containing surface; and

treating the exposed oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane at a temperature from 200°C to 500°C and a pressure from 1 Torr to 100 Torr for at least 1 second, any layer deposited by the treating being no more than 3 monolayers thick; and

forming a second capacitor electrode consisting essentially of metal over the treated oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated oxide-containing surface.